SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

S1806

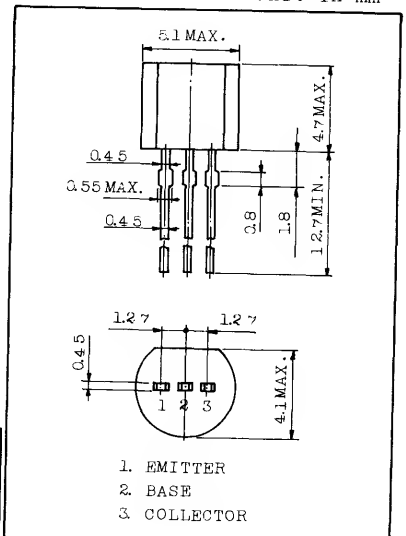
DESIGNED FOR USE IN AUDIO STAGE MEDIUM POWER AMPLIFIER.
RECOMMENDED FOR OUTPUT AMPLIFIER STAGE IN CLASS B PUSH-PULL OPERATION.

LOW FREQUENCY, MEDIUM POWER AMPLIFIERS.
DRIVER STAGE AMPLIFIERS.

FEATURES:

- Excellent h_{FE} vs. Collector Current Characteristics,
  $h_{FE(2)}$=23Min. at V_{CE}=-1V, I_C=-400mA
- Complementary to S1805.

Unit in mm



JEDEC	TO-92
EIAJ	SC-43
TOSHIBA	2-5F1F

Weight : 0.21g

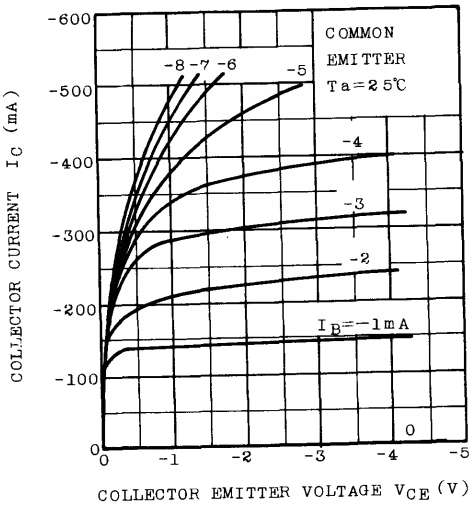
MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-500	mA
Base Current	I_B	-250	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

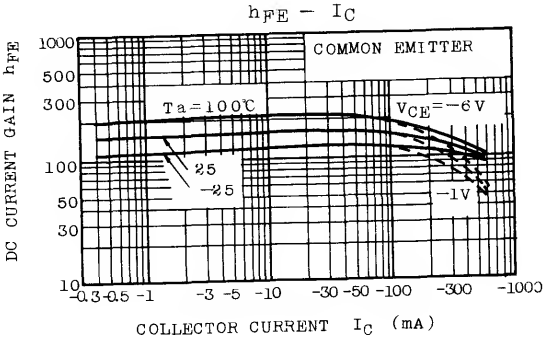
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
DC Current Gain (1)	$h_{FE(1)}$	V_{CE}=1V, I_C=-50mA	70	-	240	
DC Current Gain (2)	$h_{FE(2)}$	V_{CE}=-1V, I_C=-400mA	23	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-100mA, I_B=-5mA	-	-	-0.25	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=-100mA, I_B=-5mA	-	-	-1.2	V
Base-Emitter Voltage	V_{BE}	V_{CE}=-1V, I_C=-50mA	-0.65	-0.72	-0.80	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=-0.1mA, I_E=0	-40	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-30	-	-	V
Collector Cut-off Current	I_{CBO}	V_{CB}=-35V, I_E=0	-	-	-100	nA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V, I_C=0	-	-	-100	nA

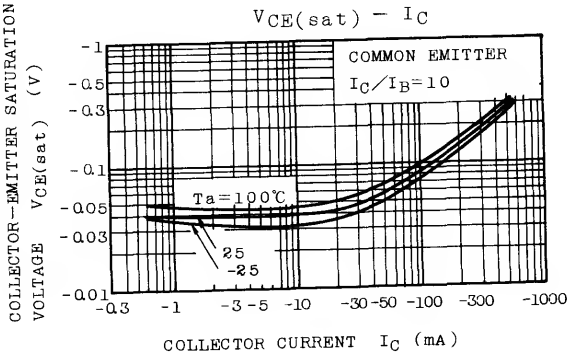
$I_C - V_{CE}$



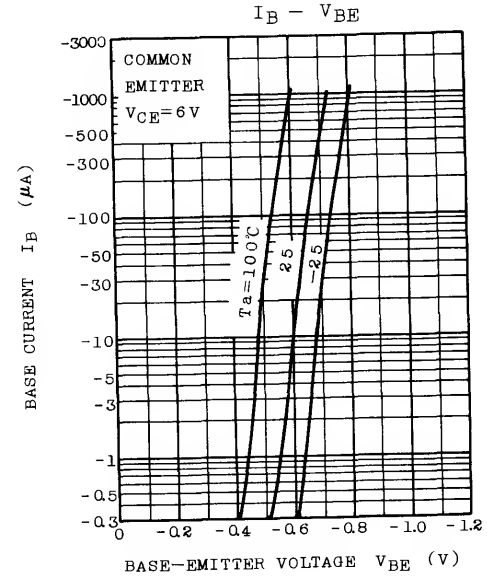
$h_{FE} - I_C$



$V_{CE(sat)} - I_C$



$I_B - V_{BE}$



$P_C - Ta$